



ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a preferably discrete bipolar transistor with a collector region, a base region, and an emitter region which are provided with connection conductors. A known means of preventing a saturation of the transistor is that the latter is provided with a Schottky clamping diode. The latter is formed in that case in that the connection conductor of the base region is also put into contact with the collector region. Here, the second connection conductor is exclusively connected to the base region, and a partial region of that portion of the base region which lies outside the emitter region, as seen in projection, lying below the second connection conductor is given a smaller flux of dopant atoms. The bipolar transistor is provided with a pn clamping diode which is formed between the partial region and the collector region.

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